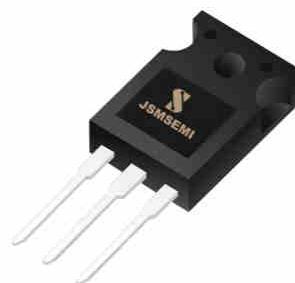


## FEATURES

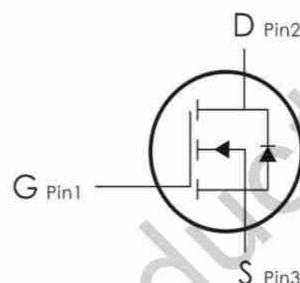
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



## APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information		
Device	Package	Marking
IRFP4668PBF	TO-247	IRFP4668



## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-247	
Drain-Source Voltage ( $V_{GS} = 0\text{ V}$ )	$V_{DSS}$	220	V
Continuous Drain Current $V_{GS} = 10\text{ V}$ $T_C = 25^\circ\text{C}$	$I_D$	130	A
Pulsed Drain Current (note1)	$I_{DM}$	530	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	1960.2	mJ
Avalanche Current (note1)	$I_{AS}$	19.8	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	1176.1	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	700	W
Peak Diode Recovery $dV/dt$ (note1)	$dv/dt$	5.0	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

## Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.89	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	60	

**Specifications  $T_J = 25^\circ\text{C}$ , unless otherwise noted**

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	220	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 40\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
		$V_{\text{DS}} = 32\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 125^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 20\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 95\text{A}$ (Note4)	--	12	27	$\text{m}\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	5784	--	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		--	893	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	561	--	
Total Gate Charge	$Q_g$	$V_{\text{DD}} = 20\text{V}, I_D = 190\text{A}, V_{\text{GS}} = 10\text{V}$ (Note4)	--	367	--	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		--	33.8	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	177	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 20\text{V}, I_D = 190\text{A}, R_G = 10 \Omega, V_{\text{GS}} = 10\text{V}$ (Note4)	--	55	--	$\text{ns}$
Turn-on Rise Time	$t_r$		--	165	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	1050	--	
Turn-off Fall Time	$t_f$		--	367	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	130	$\text{A}$
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	530	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 95\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{\text{GS}} = 0\text{V}, I_S = 190\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	360	--	$\text{ns}$
Reverse Recovery Charge	$Q_{rr}$		--	5.61	--	$\mu\text{C}$

**Notes**

- Repetitive Rating: Pulse width limited by maximum junction temperature
- $L = 10\text{mH}, V_{\text{DD}} = 50\text{V}, R_G = 25 \Omega$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )

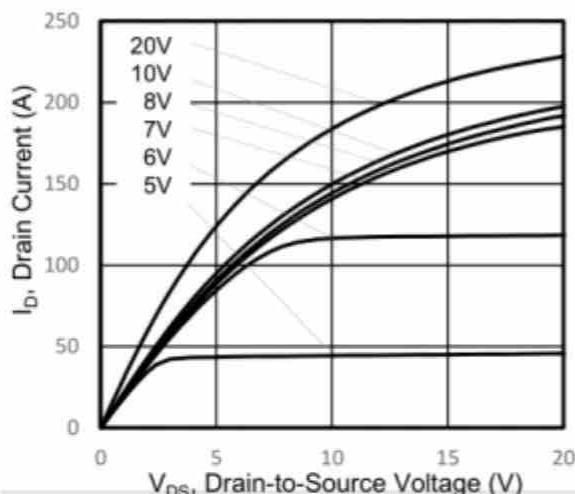


Figure 2. Body Diode Forward Voltage

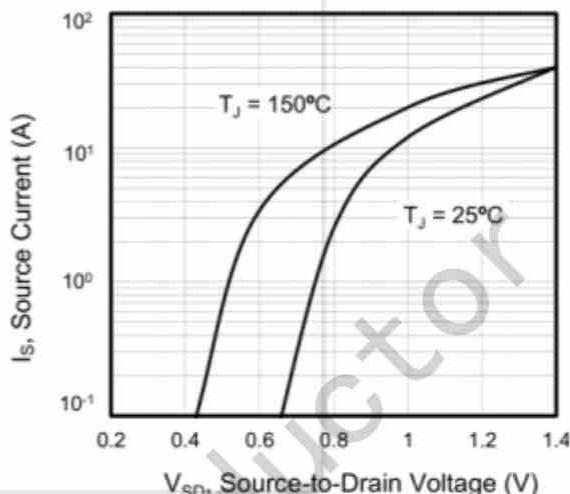


Figure 3. Drain Current vs. Temperature

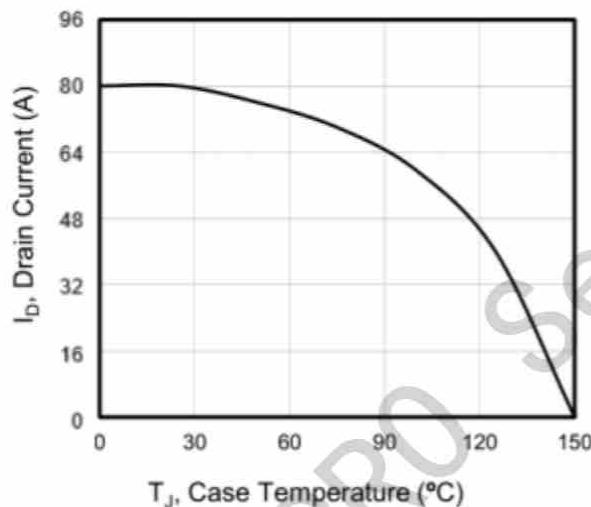


Figure 4. BV<sub>DSS</sub> Variation vs. Temperature

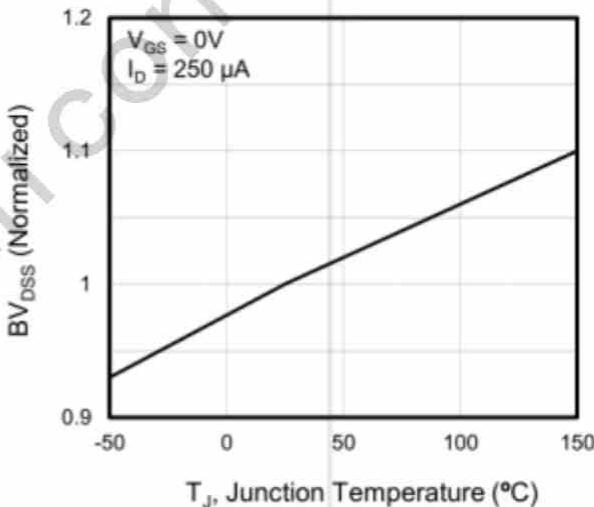


Figure 5. Transfer Characteristics

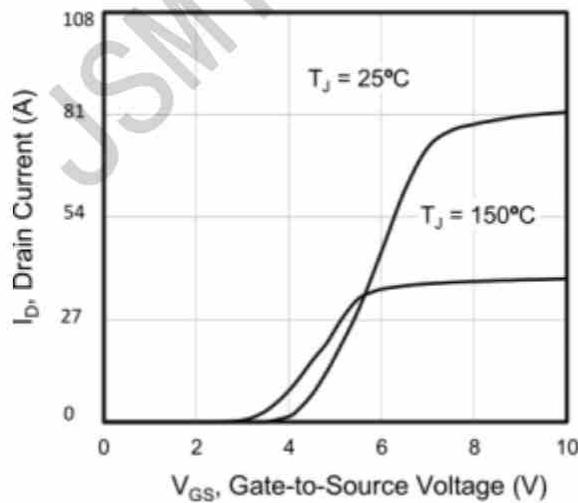
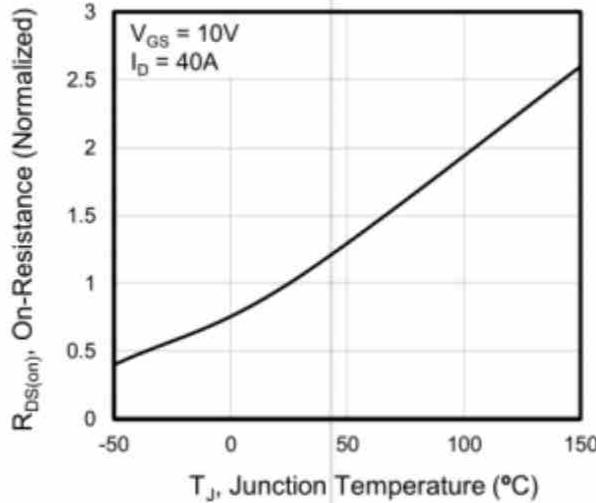


Figure 6. On-Resistance vs. Temperature



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

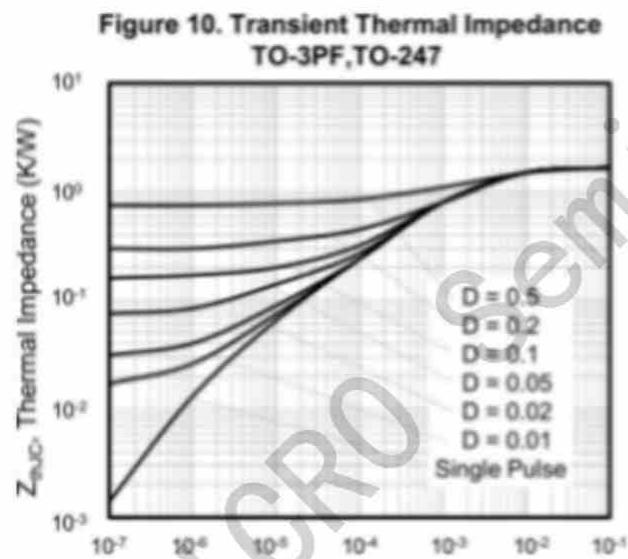
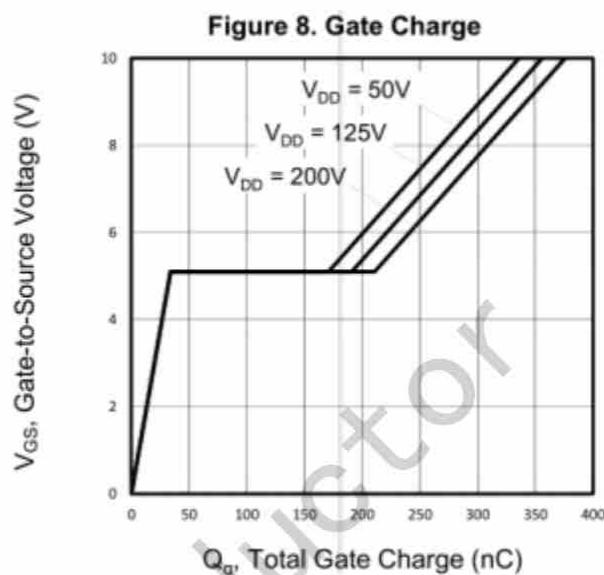
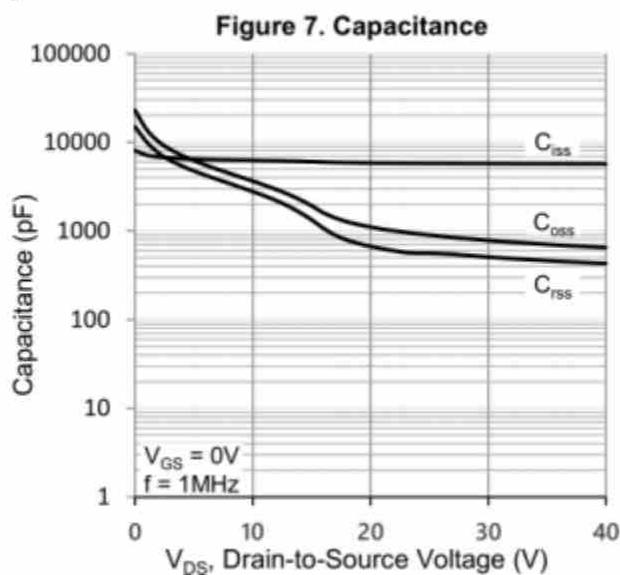


Figure A: Gate Charge Test Circuit and Waveform

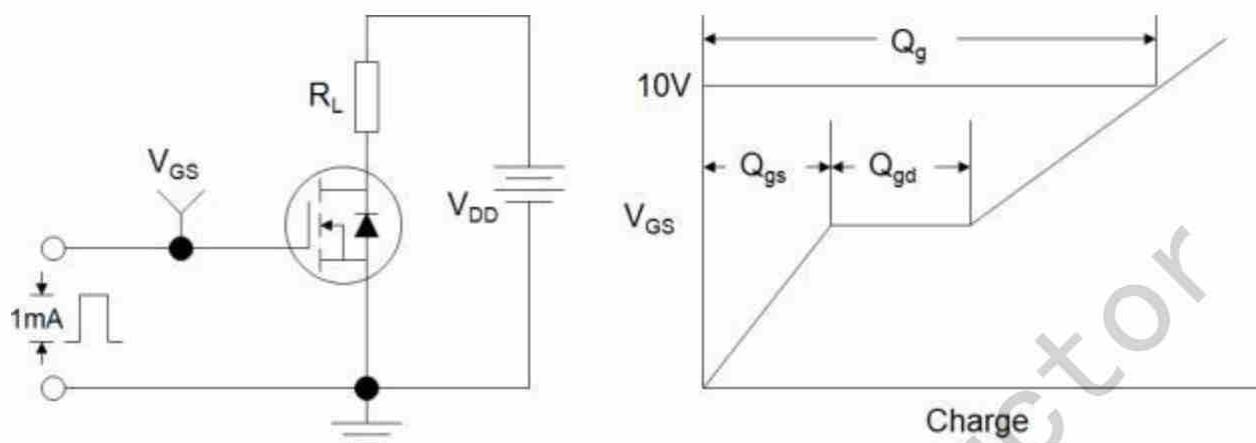


Figure B : Resistive Switching Test Circuit and Waveform

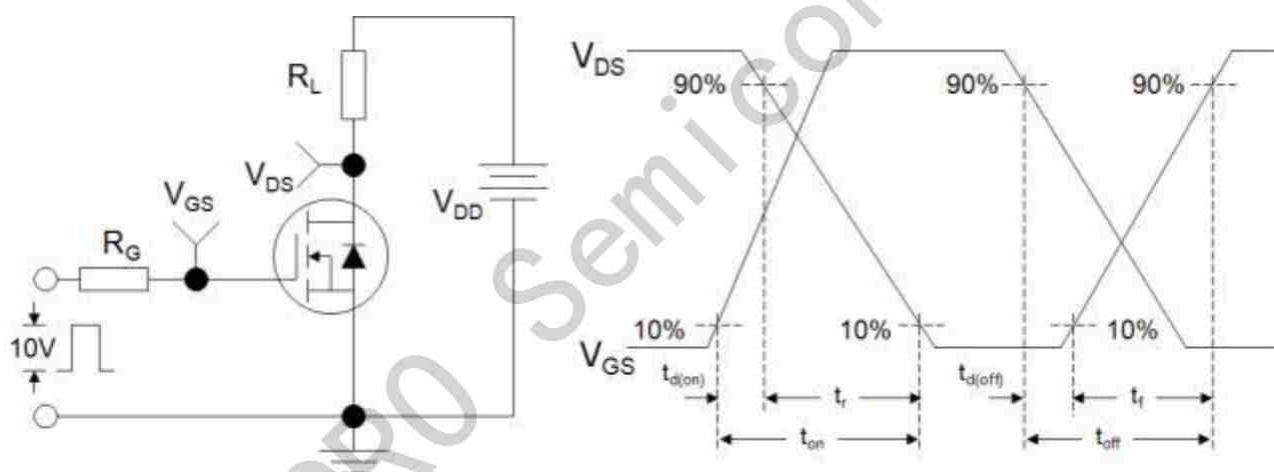
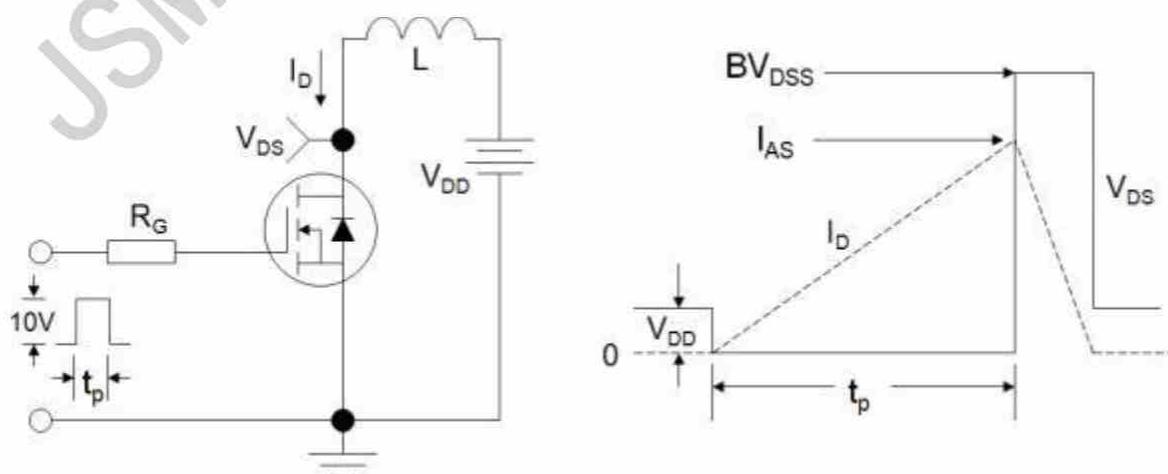
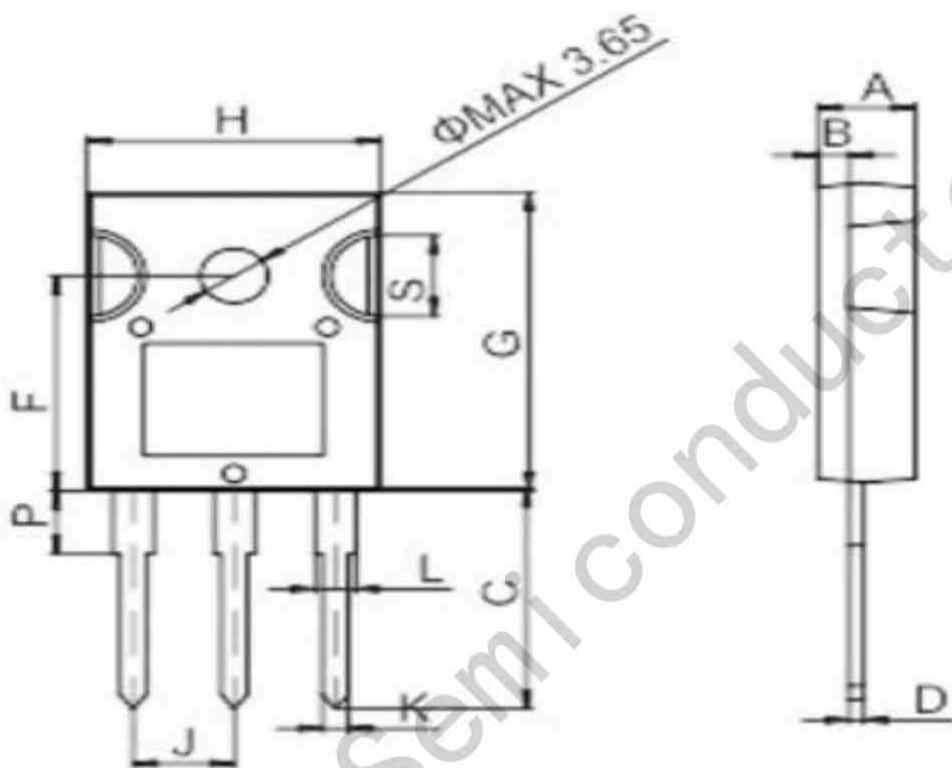


Figure C : Unclamped Inductive Switching Test Circuit and Waveform



**TO-247**


Ref.	Dimensions			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.9		5.4	0.193		0.213
B	1.6		2.0	0.063		0.079
C	14.35		15.4	0.565		0.606
D	0.5		0.8	0.020		0.031
F	14.4		15.1	0.567		0.594
G	19.7		20.6	0.775		0.811
H	15.4		16.2	0.606		0.638
J	5.3		5.6	0.209		0.220
K	1.3		1.5	0.051		0.059
L	2.8		3.3	0.110		0.130
P	3.7		4.2	0.146		0.165
S	5.35		5.65	0.211		0.222